

LISTING OF THE CURRENT CLAIMS
IN ACCORDANCE WITH REVISED AMENDMENT PRACTICE

1. (Currently Amended) A physical vapor deposition target ~~comprising~~ consisting of:
greater than or equal to 90 atomic percent copper;
a first added element, wherein the first added element is Sn; and
a second added element selected from the group consisting of Al, As, Au, B, Be, Ca, Cd, Co, Cr, Fe, Ga, Ge, Hf, Hg, Ir, Li, Mg, Mn, Nb, Ni, Pb, Pd, Pt, Sb, Sc, Si, Ta, Te, V, W, and Zn.
2. (Original) The physical vapor deposition target of claim 1 wherein a total combined amount of the first and second added elements present in the target is from at least 100 ppm to less than about 10 atomic %.

Claim 3: Canceled.

4. (Original) The physical vapor deposition target of claim 1 wherein the first and second added elements are each present in the target at 0.5 atomic percent.
5. (Original) The physical vapor deposition target of claim 1 wherein the first and second added elements are each present in the target at 0.3 atomic percent.
6. (Original) The physical vapor deposition target of claim 1 wherein the first and second added elements are present in the target in equivalent atomic percent relative to each other.

Claim 7: Canceled.

8. (Currently Amended) The physical vapor deposition target of claim [[7]] 1 wherein the second added element is Al or Zn.

9. (Currently Amended) The physical vapor deposition target of claim 1 further comprising a third added element selected from the group consisting of Al, As, Au, B, Be, Ca, Cd, Co, Cr, Fe, Ga, Ge, Hf, Hg, In, Ir, Li, Mg, Mn, Nb, Ni, Pb, Pd, Pt, Sb, Sc, Si, Ta, Te, V, W, and Zn.
10. (Original) The physical vapor deposition target of claim 9 wherein the target consists essentially of copper and the first, second and third added elements.
11. (Currently Amended) A physical vapor deposition target ~~comprising~~ consisting of: copper; and at least two elements selected from the group consisting of Al, As, Au, B, Be, Ca, Cd, Co, Cr, Fe, Ga, Ge, Hf, Hg, Ir, Li, Mg, Mn, Nb, Ni, Pb, Pd, Pt, Sb, Sc, Si, Sn, Ta, Te, V, W, and Zn, a total amount of the at least two elements present in the target being from at least 100 ppm to less than about 1 atomic %.
12. (Previously Presented) The physical vapor deposition target of claim 11 wherein the total amount of the at least two elements is from about 1000 ppm to less than about 1 atomic percent.
13. (Previously Presented) The physical vapor deposition target of claim 11 wherein the at least two elements include one or more of Sn, Al, and Zn.
14. (Original) The physical vapor deposition target of claim 11 wherein the target comprises a ternary mixture of copper and two additional elements.
15. (Original) The physical vapor deposition target of claim 14 wherein the target consists essentially of the ternary mixture.
16. (Original) The physical vapor deposition target of claim 14 wherein the ternary mixture is a ternary alloy.
17. (Currently Amended) An interconnect comprising a mixture of copper and two or more elements selected from the group consisting of Al, As, Au, B, Be, Ca, Cd,

Co, Cr, Fe, Ga, Ge, Hf, Hg, Ir, Li, Mg, Mn, Nb, Ni, Pb, Pd, Pt, Sb, Sc, Si, Sn, Ta, Te, V, W, and Zn, a total amount of the at least two elements present in the interconnect being from at least 100 ppm to less than about 10 atomic %.

18. (Original) The interconnect of claim 17 wherein the two or more elements includes a first element and a second element, the first and second elements being present in atomic equivalent amounts within the mixture relative to each other.
19. (Original) The interconnect of claim 18 wherein the first and second elements are each present in the mixture at 0.5 atomic percent.
20. (Original) The interconnect of claim 18 wherein the first and second elements are each present in the mixture at 0.3 atomic percent.
21. (Currently Amended) A thin film comprising a mixture of copper and two or more elements selected from the group consisting of Al, As, Au, B, Be, Ca, Cd, Co, Cr, Fe, Ga, Ge, Hf, Hg, Ir, Li, Mg, Mn, Nb, Ni, Pb, Pd, Pt, Sb, Sc, Si, Sn, Ta, Te, V, W, and Zn, a total amount of the at least two elements present in the thin film being from at least 100 ppm to less than about 10 atomic %.
22. (Original) The thin film of claim 21 wherein the mixture is a ternary mixture.
23. (Previously Presented) The thin film of claim 21 wherein the mixture comprises Sn as a first element, and a second element selected from Zn and Al.
24. (Original) The thin film of claim 23 wherein the first and second elements are present in the mixture at an equivalent atomic percent relative to each other.

Claims 25-31: Canceled.